

2SK1487

FIELD EFFECT TRANSISTOR
SILICON N CHANNEL MOS TYPE (π -MOSIII-5)

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS.
DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS.

INDUSTRIAL APPLICATIONS

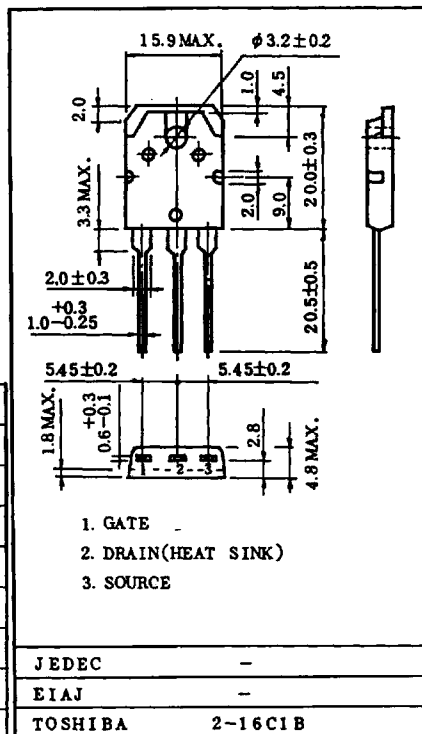
Unit in mm

FEATURES:

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 0.64\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 4.5S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 300\mu A$ (Max.) @ $V_{DS} = 450V$
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0V$ @ $V_{DS} = 10V, I_D = 1mA$

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	450	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	450	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	DC	I_D	10	A
	Pulse	I_{DP}	40	A
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	125	W
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$



Weight : 4.6g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	1.0	$^\circ C/W$
Thermal Resistance, Channel To Ambient	$R_{th(ch-a)}$	50	$^\circ C/W$

THIS TRANSISTOR IS AN ELECTROSTATIC DEVICE. PLEASE HANDLE WITH CAUTION.

ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I _{GSS}	V _{GS} = ±25V, V _{DS} =0V	—	—	±100	nA
Drain Cut-off Current		I _{DSS}	V _{DS} =450V, V _{GS} =0V	—	—	300	μA
Drain-Source Breakdown Voltage		V(BR) _{DSS}	I _D =10mA, V _{GS} =0V	450	—	—	V
Gate Threshold Voltage		V _{th}	V _{DS} =10V, I _D =1mA	2.0	—	4.0	V
Drain-Source ON Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =5A	—	0.64	1.0	Ω
Forward Transfer Admittance		Y _{fs}	V _{DS} =10V, I _D =5A	3.0	4.5	—	S
Input Capacitance		C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHz	—	840	1100	pF
Reverse Transfer Capacitance		C _{rss}		—	140	250	
Output Capacitance		C _{oss}		—	230	300	
Switching Time	Rise Time	t _r		—	45	90	ns
	Turn-on Time	t _{on}		—	70	140	
	Fall Time	t _f		—	65	130	
	Turn-off Time	t _{off}		—	150	300	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q _g	V _{DD} ≈ 400V, V _{GS} =10V, I _D =10A	—	72	85	nC
Gate-Source Charge		Q _{gs}		—	28	—	
Gate-Drain(" Miller")Charge		Q _{gd}		—	44	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS(Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I _{DR}	----	—	—	10	A
Pulse Drain Reverse Current	I _{DRP}	----	—	—	40	A
Diode Forward Voltage	V _{DSF}	I _{DR} =10A, V _{GS} =0V	—	—	-2.0	V
Reverse Recovery Time	t _{rr}	I _{DR} =10A, V _{GS} =0V	—	800	—	ns
Reverse Recovered Charge	Q _{rr}	d I _{DR} /dt =100A/μs	—	3.7	—	μC